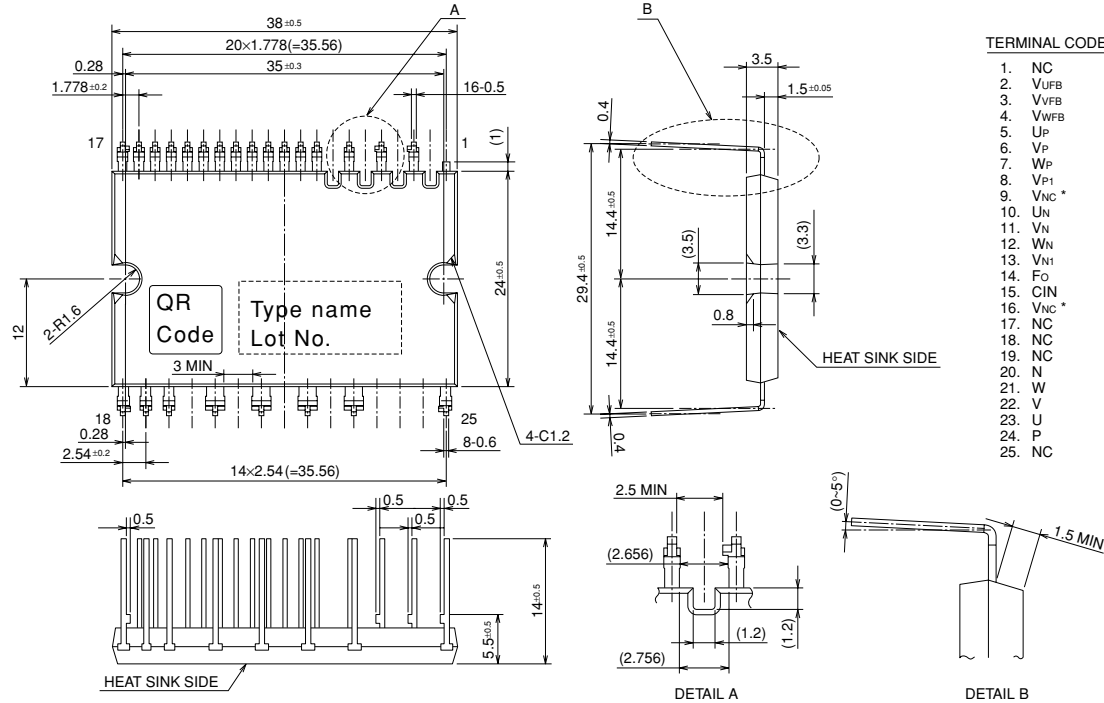


PS21963-4E/-4AE/-4CE/-4EW

TRANSFER-MOLD TYPE
INSULATED TYPE

Fig. 2 LONG TERMINAL TYPE PACKAGE OUTLINES (PS21963-4AE)

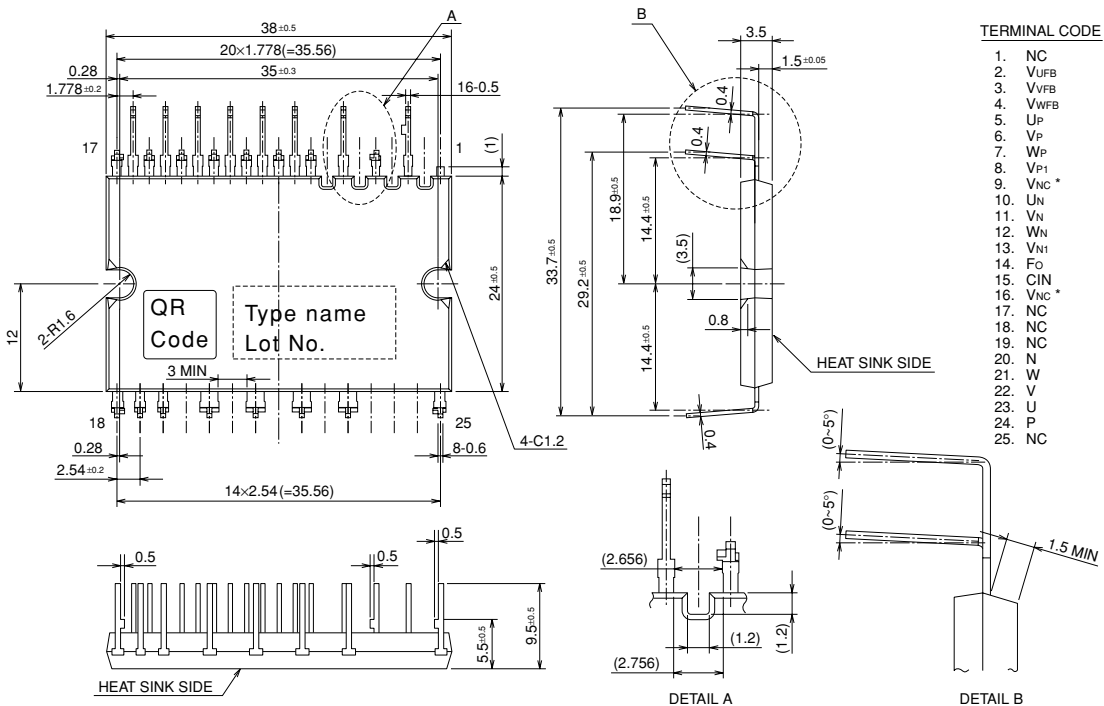
Dimensions in mm



*) Two VNC terminals (9 & 16 pin) are connected inside DIP-IPM, please connect either one to the 15V power supply GND outside and leave another one open.

Fig. 3 ZIGZAG TERMINAL TYPE PACKAGE OUTLINES (PS21963-4CE)

Dimensions in mm



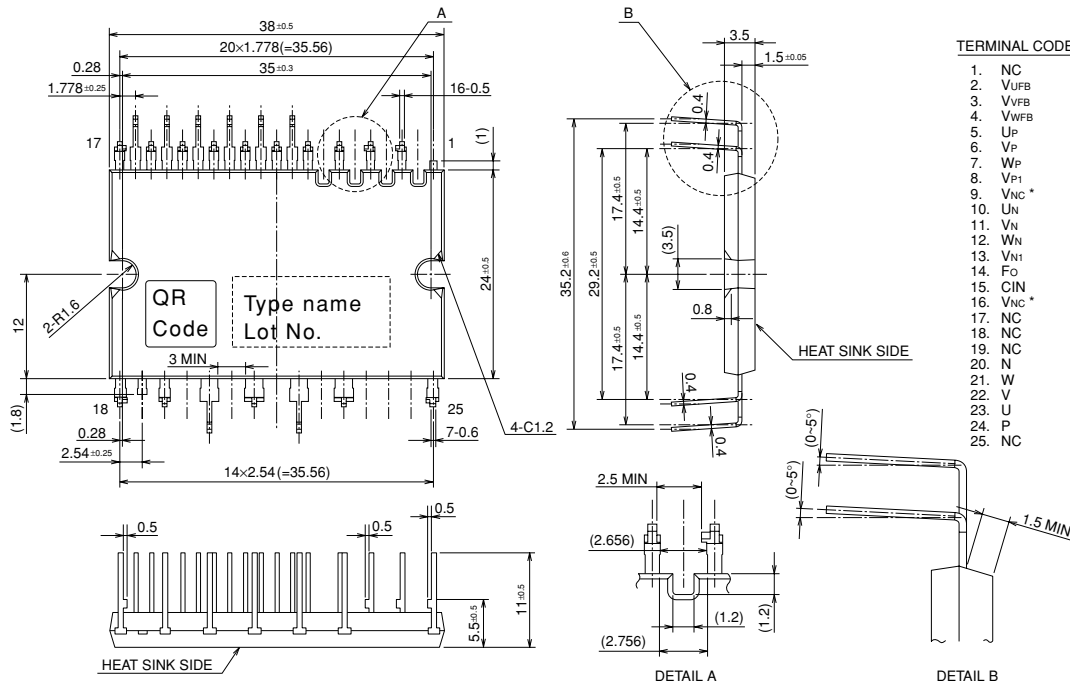
*) Two VNC terminals (9 & 16 pin) are connected inside DIP-IPM, please connect either one to the 15V power supply GND outside and leave another one open.

PS21963-4E/-4AE/-4CE/-4EW

TRANSFER-MOLD TYPE
INSULATED TYPE

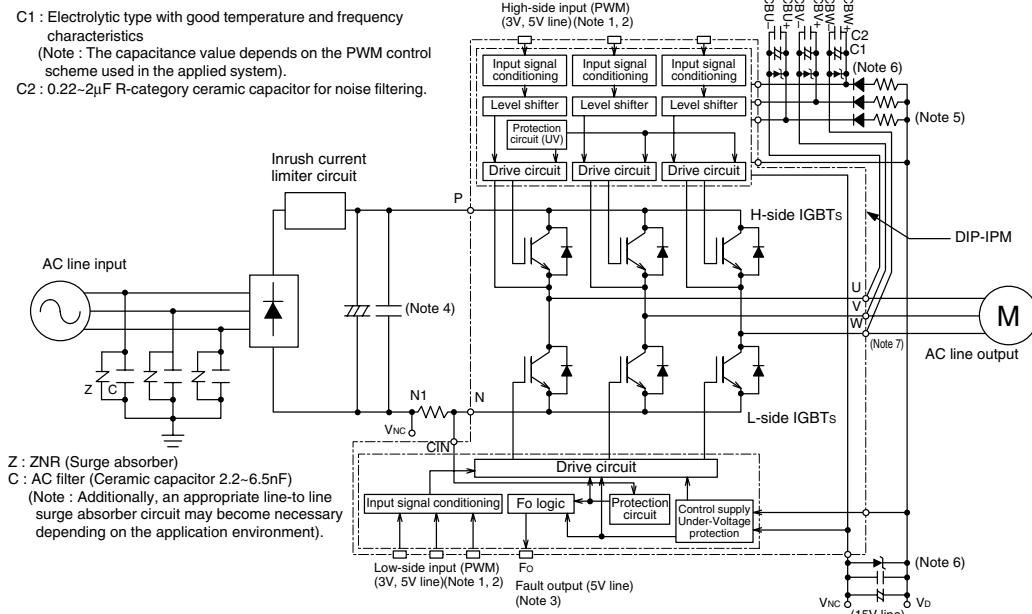
Fig. 4 BOTH SIDES ZIGZAG TERMINAL TYPE PACKAGE OUTLINES (PS21963-4EW)

Dimensions in mm



*) Two V_{NC} terminals (9 & 16 pin) are connected inside DIP-IPM, please connect either one to the 15V power supply GND outside and leave another one open.

Fig. 5 INTERNAL FUNCTIONS BLOCK DIAGRAM (TYPICAL APPLICATION EXAMPLE)

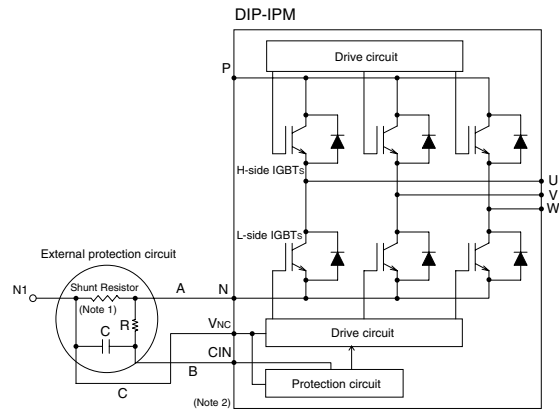


- Note1:** Input logic is high-active. There is a 3.3kΩ (min) pull-down resistor built-in each input circuit. When using an external CR filter, please make it satisfy the input threshold voltage.
- 2:** By virtue of integrating an application specific type HVIC inside the module, direct coupling to MCU terminals without any opto-coupler or transformer isolation is possible. (see also Fig. 11)
- 3:** This output is open drain type. The signal line should be pulled up to the positive side of the 5V power supply with approximately 10kΩ resistor. (see also Fig. 11)
- 4:** The wiring between the power DC link capacitor and the P, N1 terminals should be as short as possible to protect the DIP-IPM against catastrophic high surge voltages. For extra precaution, a small film type snubber capacitor (0.1-0.22μF, high voltage type) is recommended to be mounted close to these P & N1 DC power input pins.
- 5:** High voltage (600V or more) and fast recovery type (less than 100ns) diodes should be used in the bootstrap circuit.
- 6:** It is recommended to insert a Zener diode (24V/1W) between each pair of control supply terminals to prevent surge destruction.
- 7:** Bootstrap negative electrodes should be connected to U, V, W terminals directly and separated from the main output wires.

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TRANSFER-MOLD TYPE
INSULATED TYPE

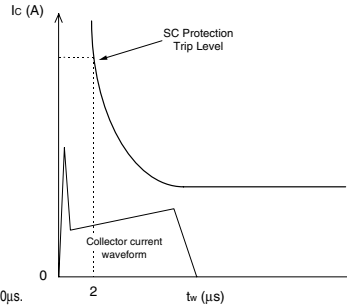
Fig. 6 EXTERNAL PART OF THE DIP-IPM PROTECTION CIRCUIT



Note1: In the recommended external protection circuit, please select the RC time constant in the range 1.5~2.0μs.
2: To prevent erroneous protection operation, the wiring of A, B, C should be as short as possible.

Short Circuit Protective Function (SC) :

SC protection is achieved by sensing the L-side DC-Bus current (through the external shunt resistor) after allowing a suitable filtering time (defined by the RC circuit). When the sensed shunt voltage exceeds the SC trip-level, all the L-side IGBTs are turned OFF and a fault signal (Fo) is output. Since the SC fault may be repetitive, it is recommended to stop the system when the Fo signal is received and check the fault.



MAXIMUM RATINGS (Tj = 25°C, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Condition	Ratings	Unit
VCC	Supply voltage	Applied between P-N	450	V
VCC(surge)	Supply voltage (surge)	Applied between P-N	500	V
VCEs	Collector-emitter voltage		600	V
±Ic	Each IGBT collector current	Tc = 25°C	8	A
±ICP	Each IGBT collector current (peak)	Tc = 25°C, less than 1ms	16	A
Pc	Collector dissipation	Tc = 25°C, per 1 chip	24.3	W
Tj	Junction temperature	(Note 1)	-20~+125	°C

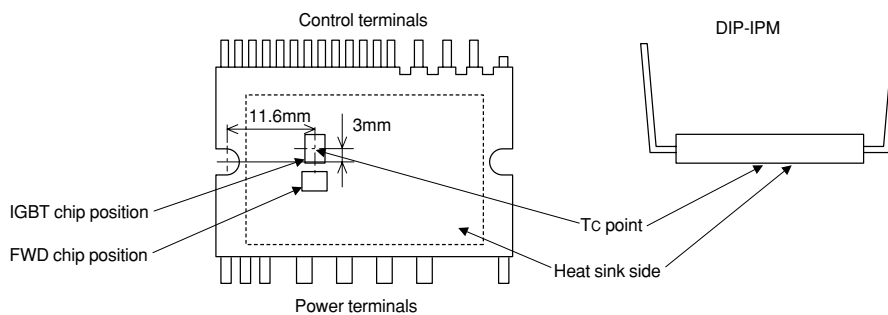
Note 1 : The maximum junction temperature rating of the power chips integrated within the DIP-IPM is 150°C (@ Tc ≤ 100°C). However, to ensure safe operation of the DIP-IPM, the average junction temperature should be limited to Tj(ave) ≤ 125°C (@ Tc ≤ 100°C).

CONTROL (PROTECTION) PART

Symbol	Parameter	Condition	Ratings	Unit
VD	Control supply voltage	Applied between VP1-VNC, VN1-VNC	20	V
VDB	Control supply voltage	Applied between VUFB-U, VVFB-V, VWFB-W	20	V
VIN	Input voltage	Applied between UP, VP, WP, UN, VN, WN-VNC	-0.5~VD+0.5	V
VFO	Fault output supply voltage	Applied between Fo-VNC	-0.5~VD+0.5	V
Ifo	Fault output current	Sink current at Fo terminal	1	mA
Vsc	Current sensing input voltage	Applied between CIN-VNC	-0.5~VD+0.5	V

PS21963-4E/-4AE/-4CE/-4EW**TRANSFER-MOLD TYPE
INSULATED TYPE****TOTAL SYSTEM**

Symbol	Parameter	Condition	Ratings	Unit
V _{CC(Prot)}	Self protection supply voltage limit (short circuit protection capability)	V _D = 13.5~16.5V, Inverter part T _j = 125°C, non-repetitive, less than 2μs	400	V
T _C	Module case operation temperature	(Note 2)	-20~+100	°C
T _{stg}	Storage temperature		-40~+125	°C
V _{iso}	Isolation voltage	60Hz, Sinusoidal, 1 minute, Between pins and heat-sink plate	1500	V _{rms}

Note 2: T_C measurement point**THERMAL RESISTANCE**

Symbol	Parameter	Condition	Limits			Unit
			Min.	Typ.	Max.	
R _{th(j-c)Q}	Junction to case thermal resistance (Note 3)	Inverter IGBT part (per 1/6 module)	—	—	4.1	°C/W
R _{th(j-c)F}		Inverter FWD part (per 1/6 module)	—	—	5.4	°C/W

Note 3: Grease with good thermal conductivity should be applied evenly with about +100μm~+200μm on the contacting surface of DIP-IPM and heat-sink.

The contacting thermal resistance between DIP-IPM case and heat sink (R_{th(c-f)}) is determined by the thickness and the thermal conductivity of the applied grease. For reference, R_{th(c-f)} (per 1/6 module) is about 0.3°C/W when the grease thickness is 20μm and the thermal conductivity is 1.0W/m·K.

ELECTRICAL CHARACTERISTICS (T_j = 25°C, unless otherwise noted)**INVERTER PART**

Symbol	Parameter	Condition		Limits			Unit
				Min.	Typ.	Max.	
V _{CE(sat)}	Collector-emitter saturation voltage	V _D = V _{DB} = 15V V _{IN} = 5V	I _C = 8A, T _j = 25°C I _C = 8A, T _j = 125°C	—	1.70 1.80	2.20 2.30	V
V _{EC}	FWD forward voltage	T _j = 25°C, -I _C = 8A, V _{IN} = 0V		—	1.90	2.35	V
t _{on}	Switching times	V _{CC} = 300V, V _D = V _{DB} = 15V		0.60	1.10	1.70	μs
t _{rr}		I _C = 8A, T _j = 125°C, V _{IN} = 0 ↔ 5V		—	0.30	—	μs
t _{c(on)}		Inductive load (upper-lower arm)		—	0.40	0.60	μs
t _{off}				—	1.40	2.00	μs
t _{c(off)}				—	0.40	0.75	μs
I _{CES}	Collector-emitter cut-off current	V _{CE} = V _{CES}	T _j = 25°C T _j = 125°C	—	—	1 10	mA

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CONTROL (PROTECTION) PART

Symbol	Parameter	Condition		Limits			Unit
				Min.	Typ.	Max.	
ID	Circuit current	VD = VDB = 15V VIN = 5V	Total of VP1-VNC, VN1-VNC	—	—	2.80	mA
			VUFB-U, VVFB-V, VWFB-W	—	—	0.55	mA
		VD = VDB = 15V VIN = 0V	Total of VP1-VNC, VN1-VNC	—	—	2.80	mA
			VUFB-U, VVFB-V, VWFB-W	—	—	0.55	mA
VFOH	Fault output voltage	VSC = 0V, Fo terminal pull-up to 5V by 10kΩ		4.9	—	—	V
VFOL		VSC = 1V, IFO = 1mA		—	—	0.95	V
VSC(ref)	Short circuit trip level	Tj = 25°C, VD = 15V (Note 4)		0.43	0.48	0.53	V
IIN	Input current	VIN = 5V		0.70	1.00	1.50	mA
UVDBt	Control supply under-voltage protection	Tj ≤ 125°C	Trip level	10.0	—	12.0	V
UVDBr			Reset level	10.5	—	12.5	V
UVDt			Trip level	10.3	—	12.5	V
UVDr			Reset level	10.8	—	13.0	V
tFO	Fault output pulse width	(Note 5)		20	—	—	μs
Vth(on)	ON threshold voltage	Applied between UP, VP, WP, UN, VN, WN-VNC		—	2.1	2.6	V
Vth(off)	OFF threshold voltage			0.8	1.3	—	V
Vth(hys)	ON/OFF threshold hysteresis voltage			0.35	0.65	—	V

Note 4 : Short circuit protection is functioning only for the lower-arms. Please select the external shunt resistance such that the SC trip-level is less than 1.7 times of the current rating.

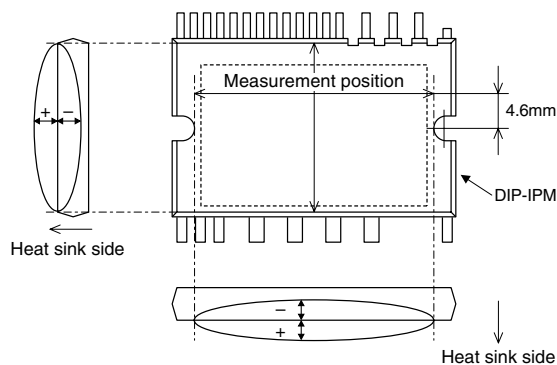
5 : Fault signal is asserted corresponding to a short circuit or lower side control supply under-voltage failure.

MECHANICAL CHARACTERISTICS AND RATINGS

Parameter	Condition	Limits			Unit
		Min.	Typ.	Max.	
Mounting torque	Mounting screw : M3 (Note 6) Recommended : 0.69 N·m	0.59	—	0.78	N·m
Weight		—	10	—	g
Heat-sink flatness	(Note 7)	−50	—	100	μm

Note 6 : Plain washers (ISO 7089~7094) are recommended.

Note 7 : Flatness measurement position



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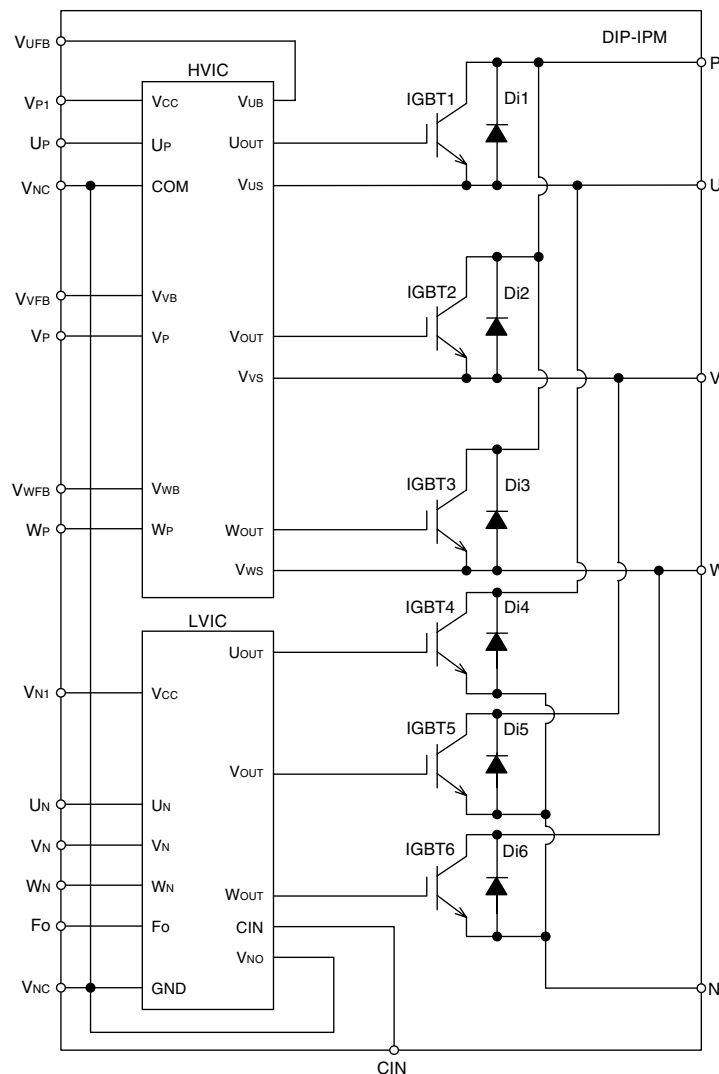
RECOMMENDED OPERATION CONDITIONS

Symbol	Parameter	Condition	Limits			Unit
			Min.	Typ.	Max.	
V _{CC}	Supply voltage	Applied between P-N	0	300	400	V
V _D	Control supply voltage	Applied between V _{P1} -V _{NC} , V _{N1} -V _{NC}	13.5	15.0	16.5	V
V _{DB}	Control supply voltage	Applied between V _{UFB} -U, V _{VFB} -V, V _{WFB} -W	13.0	15.0	18.5	V
ΔV _D , ΔV _{DB}	Control supply variation		-1	—	1	V/μs
t _{dead}	Arm shoot-through blocking time	For each input signal, T _c ≤ 100°C	1.5	—	—	μs
f _{PWM}	PWM input frequency	T _c ≤ 100°C, T _j ≤ 125°C	—	—	20	kHz
I _O	Allowable r.m.s. current	V _{CC} = 300V, V _D = V _{DB} = 15V, P.F = 0.8, sinusoidal PWM, T _j ≤ 125°C, T _c ≤ 100°C (Note 8)	f _{PWM} = 5kHz	—	4.0	Arms
			f _{PWM} = 15kHz	—	2.5	
P _{WIN(on)}	Allowable minimum input pulse width	(Note 9)	0.5	—	—	μs
P _{WIN(off)}			0.5	—	—	
V _{NC}	V _{NC} variation	Between V _{NC} -N (including surge)	-5.0	—	5.0	V

Note 8 : The allowable r.m.s. current value depends on the actual application conditions.

9 : IPM might not make response if the input signal pulse width is less than the recommended minimum value.

Fig. 7 THE DIP-IPM INTERNAL CIRCUIT



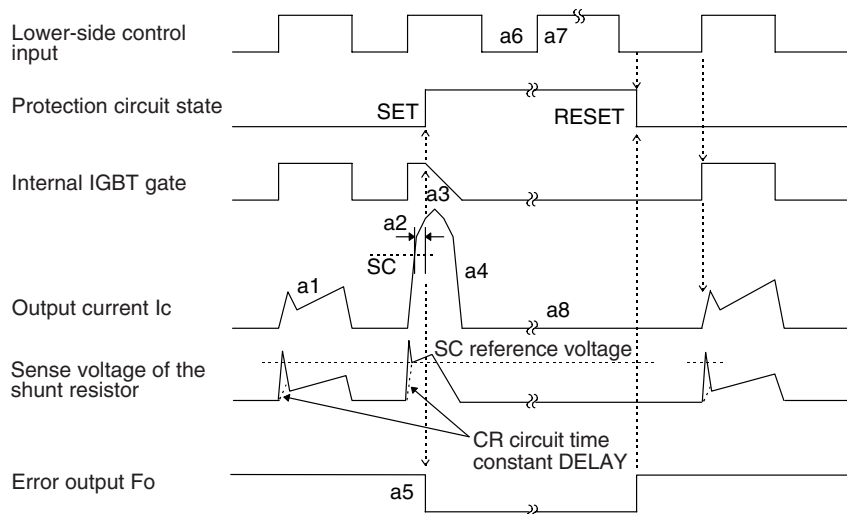
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Fig. 8 TIMING CHART OF THE DIP-IPM PROTECTIVE FUNCTIONS

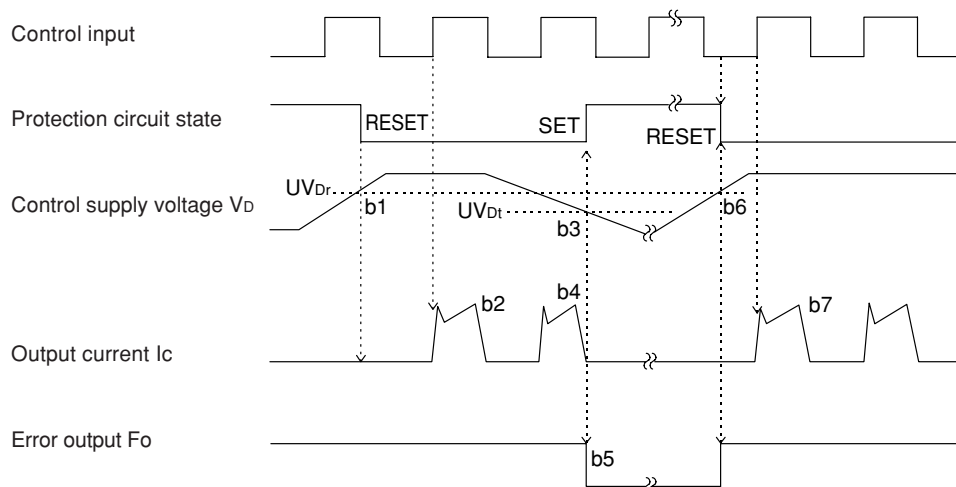
[A] Short-Circuit Protection (Lower-side only with the external shunt resistor and CR filter)

- a1. Normal operation : IGBT ON and carrying current.
- a2. Short circuit detection (SC trigger).
- a3. IGBT gate hard interruption.
- a4. IGBT turns OFF.
- a5. Fo outputs ($t_{FO(min)} = 20\mu s$).
- a6. Input "L" : IGBT OFF.
- a7. Input "H" : IGBT ON.
- a8. IGBT OFF in spite of input "H".



[B] Under-Voltage Protection (Lower-side, UV_D)

- b1. Control supply voltage rising : After the voltage level reaches UV_{Dr}, the circuits start to operate when next input is applied.
- b2. Normal operation : IGBT ON and carrying current.
- b3. Under voltage trip (UV_{Dt}).
- b4. IGBT OFF in spite of control input condition.
- b5. Fo outputs ($t_{FO} \geq 20\mu s$ and Fo outputs continuously during UV period).
- b6. Under voltage reset (UV_{Dr}).
- b7. Normal operation : IGBT ON and carrying current.



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[C] Under-Voltage Protection (Upper-side, UV_{DB})

- c1. Control supply voltage rising : After the voltage level reaches UV_{DBr}, the circuits start to operate when next input is applied.
- c2. Normal operation : IGBT ON and carrying current.
- c3. Under voltage trip (UV_{DBt}).
- c4. IGBT OFF in spite of control input signal level, but there is no Fo signal outputs.
- c5. Under voltage reset (UV_{DBr}).
- c6. Normal operation : IGBT ON and carrying current.

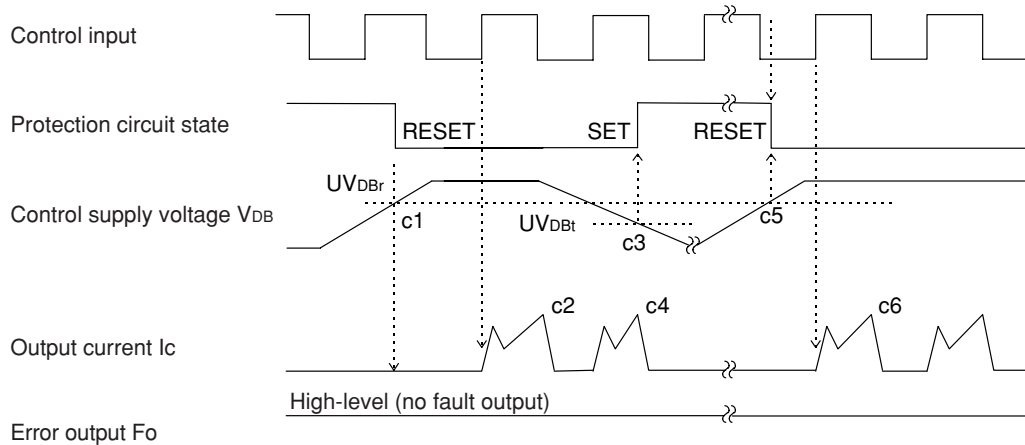
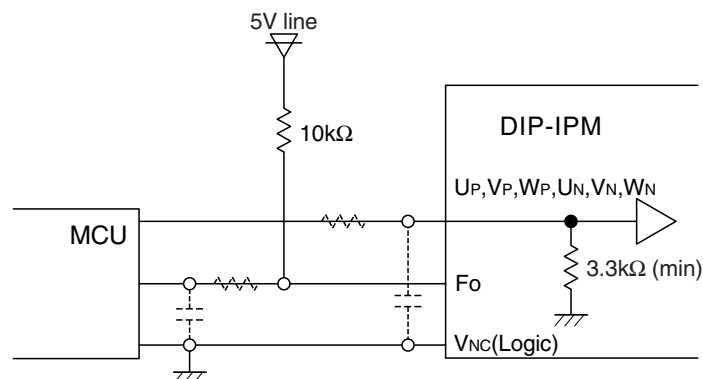
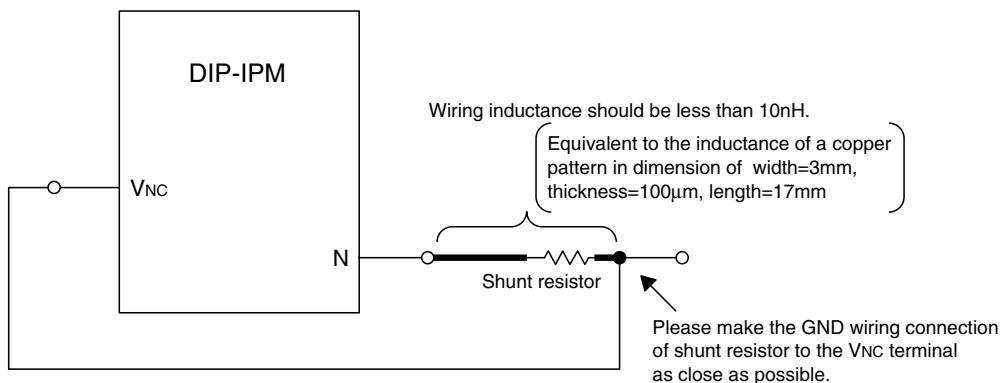


Fig. 9 RECOMMENDED MCU I/O INTERFACE CIRCUIT



Note : The setting of RC coupling at each input (parts shown dotted) depends on the PWM control scheme and the wiring impedance of the printed circuit board.
The DIP-IPM input section integrates a 3.3kΩ (min) pull-down resistor. Therefore, when using an external filtering resistor, pay attention to the turn-on threshold voltage.

Fig. 10 WIRING CONNECTION OF SHUNT RESISTOR



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